

TLP2962

1. Applications

- Factory Automation (FA)
- High-Speed Digital Interfacing
- Measuring Instruments

2. General

The Toshiba TLP2962 consists of a high-output GaAs light-emitting diode coupled with integrated high gain, high-speed photodetectors. The TLP2962 guarantees operation at up to 125 °C and on supplies from 2.7 V to 5.5 V. It is housed in the DIP8 package. The TLP2962 has an internal Faraday shield that provides a guaranteed common-mode transient immunity of 20 kV/μs.

3. Features

- (1) Inverter logic type (open collector output)
- (2) Package: DIP8
- (3) Operating temperature: -40 to 125 °C
- (4) Supply voltage: 2.7 to 5.5 V
- (5) Data transfer rate: 15 MBd (typ.) (NRZ)
- (6) Threshold input current: 5.0 mA (max)
- (7) Supply current: 4 mA (max)
- (8) Common-mode transient immunity: ±20 kV/μs (min)
- (9) Isolation voltage: 5000 Vrms (min)
- (10) Safety standards

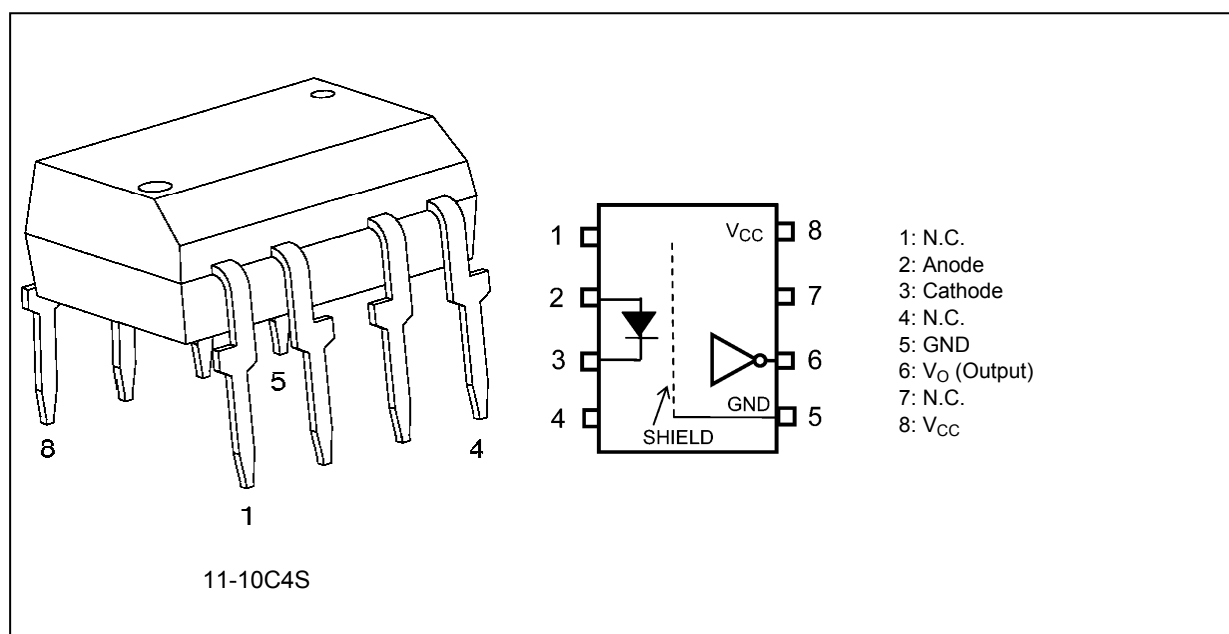
UL-approved: UL1577, File No.E67349

cUL-approved: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN60747-5-5 (**Note 1**)

Note 1: When an EN60747-5-5 approved type is needed, please designate the **Option (D4)**.

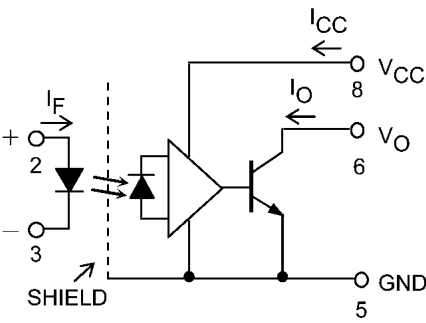
4. Packaging and Pin Configuration



Start of commercial production

2011-09

5. Internal Circuit



6. Principle of Operation

6.1. Truth Table

Input	LED	Output
H	ON	L
L	OFF	H

6.2. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	7.0	mm
Clearance distances	7.0	
Internal isolation thickness	0.4	

7. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$)

	Characteristics	Symbol	Note	Rating	Unit
LED	Input forward current	I_F		20	mA
	Input forward current derating ($T_a \geq 116\text{ }^{\circ}\text{C}$)	$\Delta I_F / \Delta T_a$		-0.6	mA/ $^{\circ}\text{C}$
	Input forward current (pulsed)	I_{FP}	(Note 1)	40	mA
	Input forward current derating (pulsed) ($T_a \geq 110\text{ }^{\circ}\text{C}$)	$\Delta I_{FP} / \Delta T_a$		-1.0	mA/ $^{\circ}\text{C}$
	Peak transient input forward current	I_{FPT}	(Note 2)	1	A
	Peak transient input forward current derating ($T_a \geq 110\text{ }^{\circ}\text{C}$)	$\Delta I_{FPT} / \Delta T_a$		-25	mA/ $^{\circ}\text{C}$
	Input power dissipation	P_D		40	mW
	Input power dissipation derating ($T_a \geq 110\text{ }^{\circ}\text{C}$)	$\Delta P_D / \Delta T_a$		-1.0	mW/ $^{\circ}\text{C}$
	Input reverse voltage	V_R		5	V
Detector	Output current	I_O		50	mA
	Output voltage	V_O		6	V
	Supply voltage	V_{CC}		6	
	Output power dissipation	P_O		85	mW
	Output power dissipation derating ($T_a \geq 110\text{ }^{\circ}\text{C}$)	$\Delta P_O / \Delta T_a$		-2.1	mW/ $^{\circ}\text{C}$
Common	Operating temperature	T_{opr}		-40 to 125	$^{\circ}\text{C}$
	Storage temperature	T_{stg}		-55 to 150	
	Lead soldering temperature (10 s)	T_{sol}		260	
	Isolation voltage AC, 60 s, R.H. $\leq 60\%$	BV_S	(Note 3)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Pulse width (PW) $\leq 1\text{ ms}$, duty = 50 %

Note 2: Pulse width (PW) $\leq 1\text{ }\mu\text{s}$, 300 pps

Note 3: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Typ.	Max	Unit
Input on-state current	$I_{F(ON)}$	(Note 1)	6.3	—	15	mA
Input off-state voltage	$V_{F(OFF)}$		0	—	0.8	V
Supply voltage	V_{CC}	(Note 2)	2.7	3.3/5.0	5.5	
Operating temperature	T_{opr}	(Note 2)	-40	—	125	$^{\circ}\text{C}$

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

Note: A ceramic capacitor (0.1 μF) should be connected between pin 8 and pin 5 to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μs .

Note 2: Denotes the operating range, not the recommended operating condition.

9. Electrical Characteristics (Note)

(Unless otherwise specified, $T_a = -40$ to $125\text{ }^{\circ}\text{C}$, $V_{CC} = 2.7$ to 5.5 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input forward voltage	V_F		—	$I_F = 10\text{ mA}$, $T_a = 25\text{ }^{\circ}\text{C}$	1.45	1.55	1.7	V
Input forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$		—	$I_F = 10\text{ mA}$	—	-2.0	—	mV/ $^{\circ}\text{C}$
Input reverse current	I_R		—	$V_R = 5\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$	—	—	10	μA
Input capacitance	C_t		—	$V = 0\text{ V}$, $f = 1\text{ MHz}$, $T_a = 25\text{ }^{\circ}\text{C}$	—	60	—	pF
High-level output current	I_{OH}		Fig. 12.1.1	$V_F = 0.8\text{ V}$, $V_O = 5.5\text{ V}$, $V_{CC} = 5.5\text{ V}$	—	—	50	μA
				$V_F = 0.8\text{ V}$, $V_O = 5.5\text{ V}$, $V_{CC} = 5.5\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$	—	—	10	
Low-level output voltage	V_{OL}		Fig. 12.1.2	$I_F = 5\text{ mA}$ $I_O = 13\text{ mA}$ (Sinking)	—	0.23	0.6	V
High-level supply current	I_{CCH}		Fig. 12.1.3	$I_F = 0\text{ mA}$	—	1.6	4.0	mA
Low-level supply current	I_{CCL}		Fig. 12.1.4	$I_F = 10\text{ mA}$	—	1.8	4.0	
Threshold input current (H/L)	I_{FHL}		—	$I_O = 13\text{ mA}$ (Sinking), $V_O < 0.6\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$	—	1.3	2.8	
				$I_O = 13\text{ mA}$ (Sinking), $V_O < 0.6\text{ V}$	—	—	5.0	

Note: All typical values are at $T_a = 25\text{ }^{\circ}\text{C}$.

10. Isolation Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$)

Characteristics	Symbol	Note	Test Conditions	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	—	1.0	—	pF
Isolation resistance	R_S	(Note 1)	$V_S = 500\text{ V}$, R.H. $\leq 60\%$	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	5000	—	—	Vrms
			AC, 1 s in oil	—	10000	—	
			DC, 60 s in oil	—	10000	—	Vdc

Note 1: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

11. Switching Characteristics (Note)

(Unless otherwise specified, $T_a = -40$ to $125\text{ }^{\circ}\text{C}$, $V_{CC} = 2.7$ to 5.5 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Propagation delay time (H/L)	t_{pHL}	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 7.5\text{ mA}$, $R_L = 350\text{ }\Omega$, $C_L = 15\text{ pF}$	—	35	75	ns
Propagation delay time (L/H)	t_{pLH}	(Note 1)		$I_F = 7.5 \rightarrow 0\text{ mA}$, $R_L = 350\text{ }\Omega$, $C_L = 15\text{ pF}$	—	25	75	
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)		$I_F = 7.5\text{ mA}$, $R_L = 350\text{ }\Omega$, $C_L = 15\text{ pF}$	—	—	35	
Propagation delay skew (device to device)	t_{psk}	(Note 1), (Note 2)			-40	—	40	
Fall time	t_f	(Note 1)		$I_F = 0 \rightarrow 7.5\text{ mA}$, $R_L = 350\text{ }\Omega$, $C_L = 15\text{ pF}$	—	3	—	
Rise time	t_r	(Note 1)		$I_F = 7.5 \rightarrow 0\text{ mA}$, $R_L = 350\text{ }\Omega$, $C_L = 15\text{ pF}$	—	12	—	
Common-mode transient immunity at output high	CM_H		Fig. 12.1.6	$V_{CM} = 1000\text{ V}_{p-p}$, $I_F = 0\text{ mA}$, $V_{CC} = 3.3\text{ V} / 5\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$	± 20	± 25	—	kV/ μs
Common-mode transient immunity at output low	CM_L			$V_{CM} = 1000\text{ V}_{p-p}$, $I_F = 10\text{ mA}$, $V_{CC} = 3.3\text{ V} / 5\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$	± 20	± 25	—	

Note: All typical values are at $T_a = 25\text{ }^{\circ}\text{C}$.Note 1: $f = 5\text{ MHz}$, duty = 50 %, input current $t_r = t_f = 5\text{ ns}$, C_L is approximately 15 pF which includes probe and stray wiring capacitance.Note 2: The propagation delay skew, t_{psk} , is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

12. Test Circuits and Characteristics Curves

12.1. Test Circuits

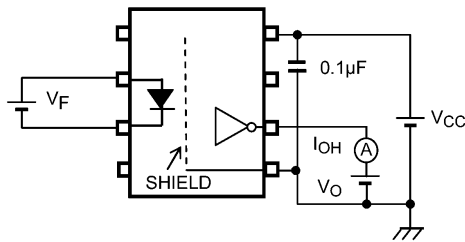


Fig. 12.1.1 I_{OH} Test Circuit

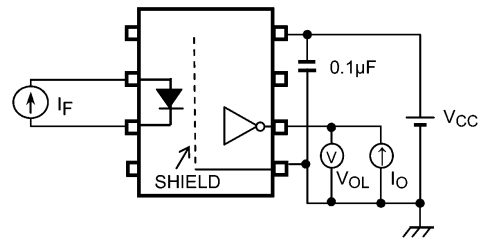


Fig. 12.1.2 V_{OL} Test Circuit

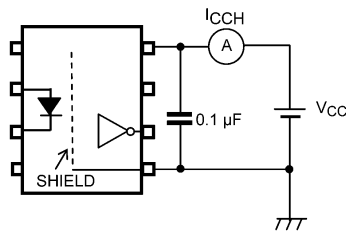


Fig. 12.1.3 I_{CCH} Test Circuit

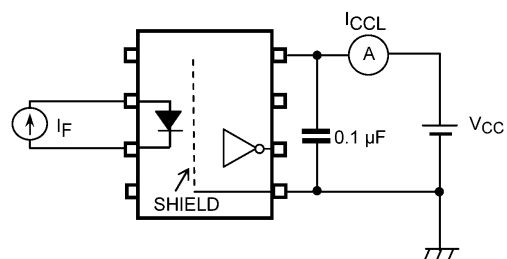
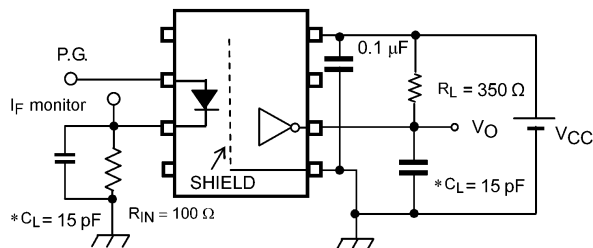


Fig. 12.1.4 I_{CCL} Test Circuit

$I_F = 7.5 \text{ mA (P.G.)}$

($f = 5 \text{ MHz}$, duty = 50 %, $t_r = t_f = \text{less than } 5 \text{ ns}$)



* C_L : includes probe and stray wiring capacitance.

P.G.: Pulse Generator

Fig. 12.1.5 Switching Time Test Circuit and Waveform

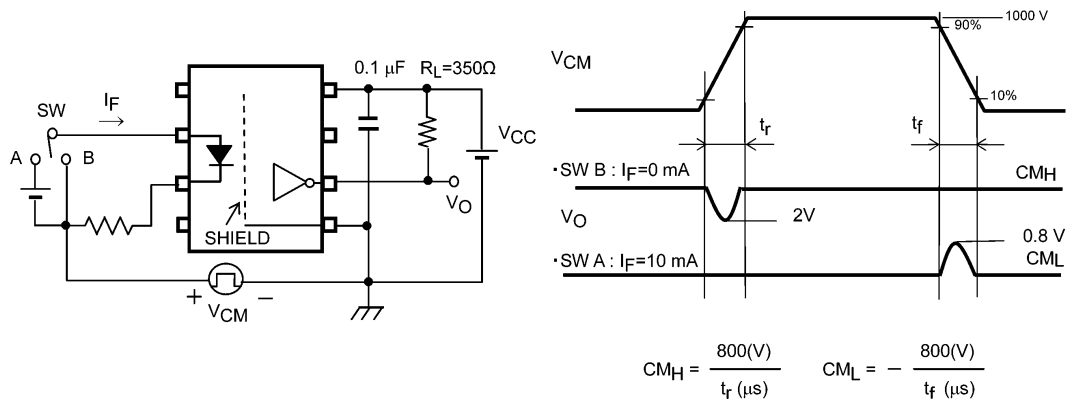


Fig. 12.1.6 Common-Mode Transient Immunity Test Circuit and Waveform

12.2. Characteristics Curves (Note)

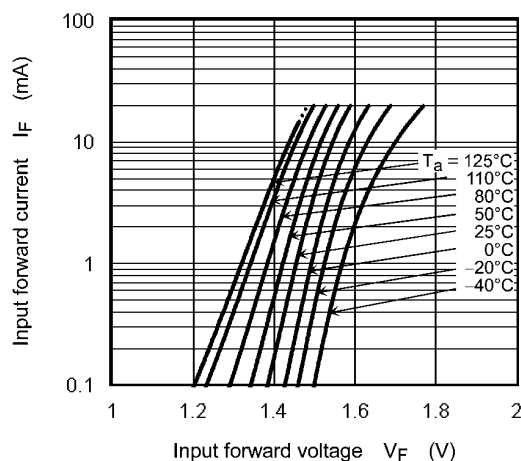


Fig. 12.2.1 $I_F - V_F$

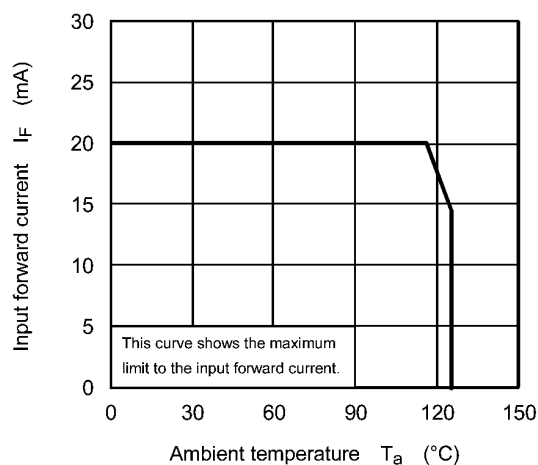


Fig. 12.2.2 $I_F - T_a$

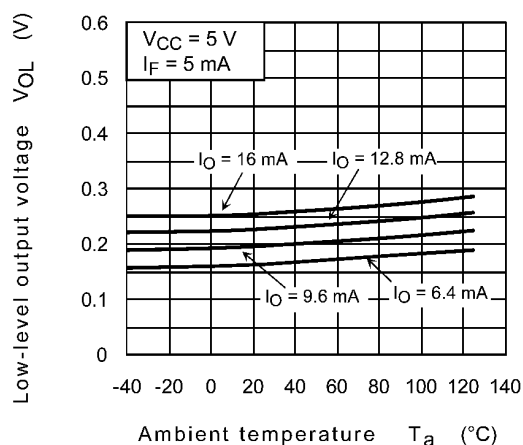


Fig. 12.2.3 $V_{OL} - T_a$

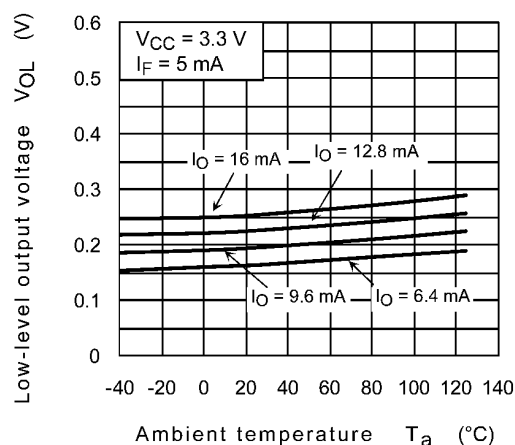


Fig. 12.2.4 $V_{OL} - T_a$

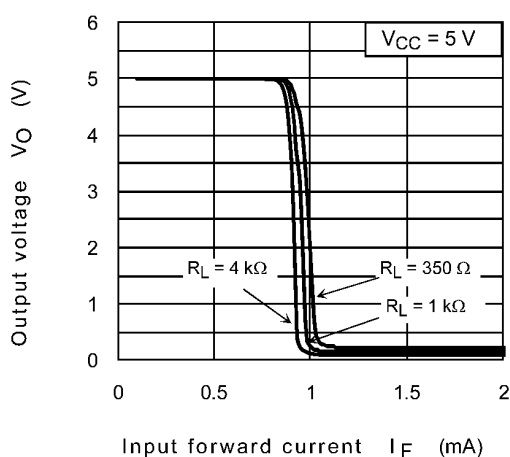


Fig. 12.2.5 $V_O - I_F$

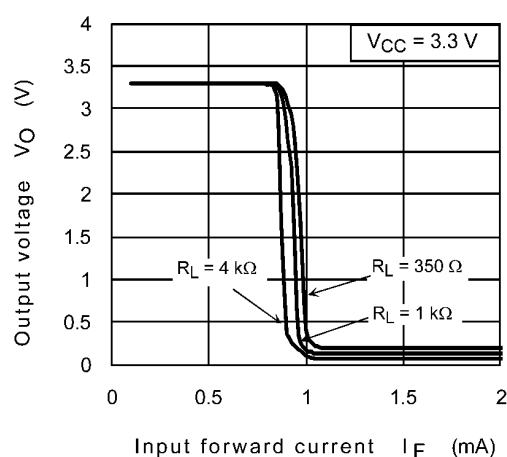


Fig. 12.2.6 $V_O - I_F$

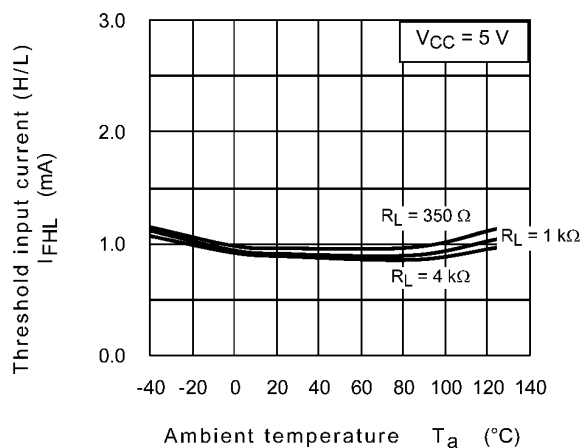


Fig. 12.2.7 $I_{FHL} - T_a$

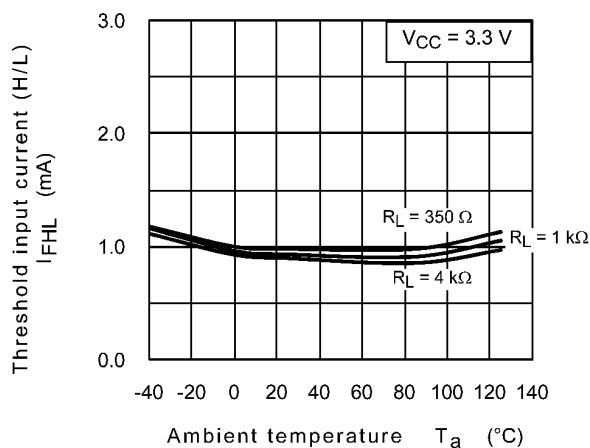


Fig. 12.2.8 $I_{FHL} - T_a$

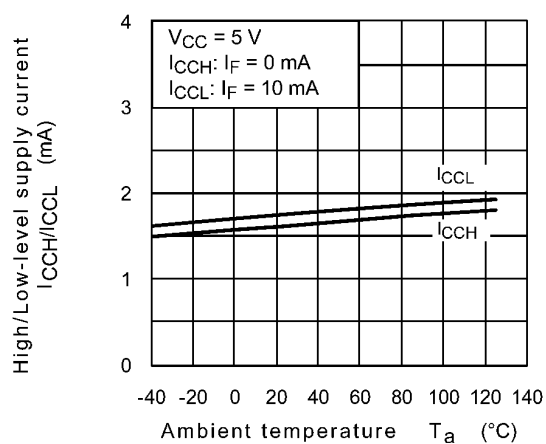


Fig. 12.2.9 $I_{CCH}, I_{CCL} - T_a$

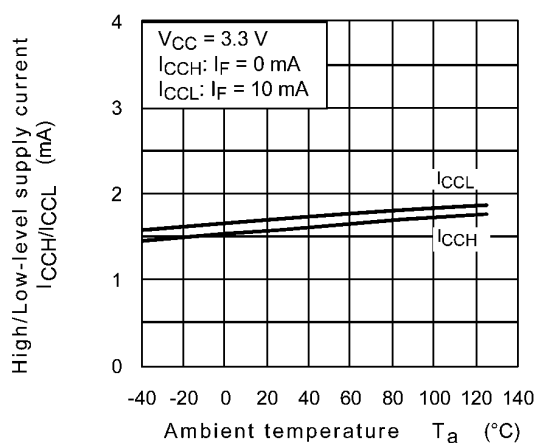


Fig. 12.2.10 $I_{CCH}, I_{CCL} - T_a$

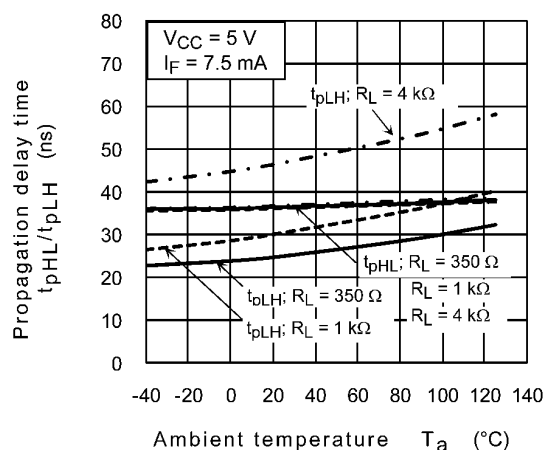


Fig. 12.2.11 $t_{pHL}, t_{pLH} - T_a$

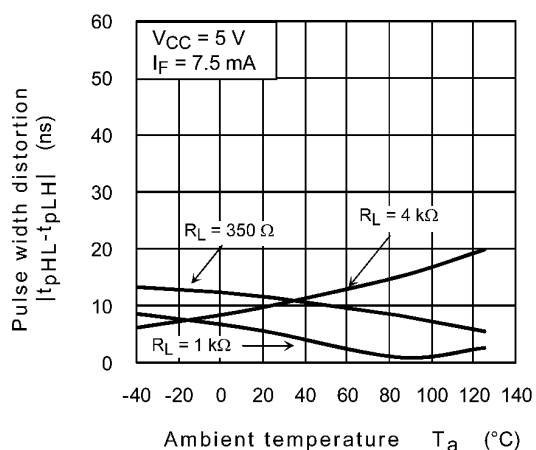


Fig. 12.2.12 $|t_{pHL} - t_{pLH}| - T_a$

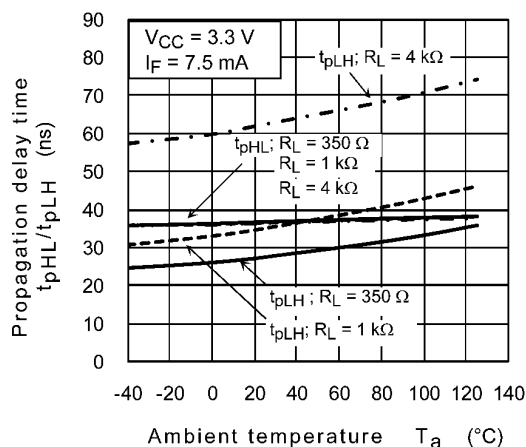


Fig. 12.2.13 t_{pHL} , t_{pLH} - T_a

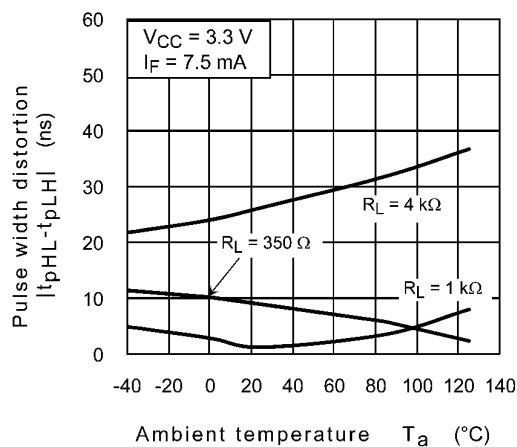


Fig. 12.2.14 $|t_{pHL} - t_{pLH}|$ - T_a

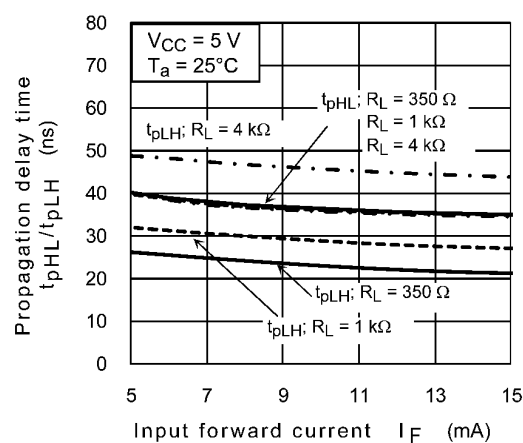


Fig. 12.2.15 t_{pHL} , t_{pLH} - I_F

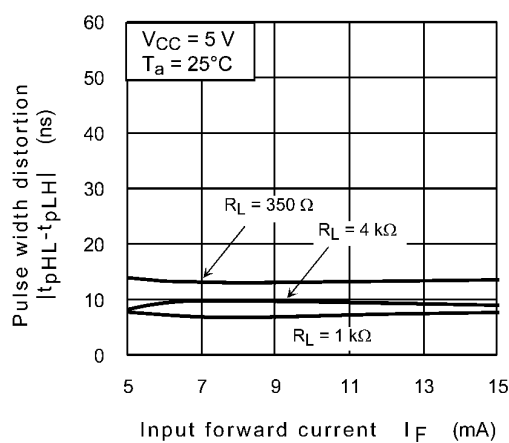


Fig. 12.2.16 $|t_{pHL} - t_{pLH}|$ - I_F

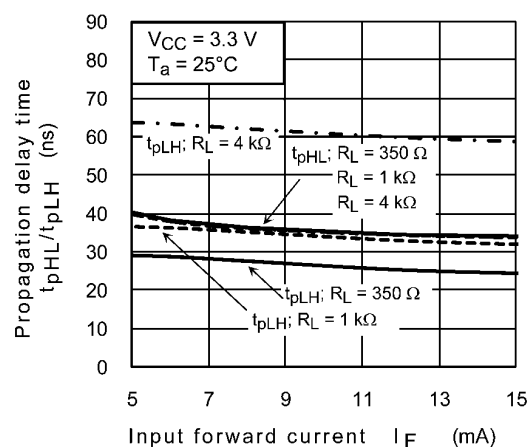


Fig. 12.2.17 t_{pHL} , t_{pLH} - I_F

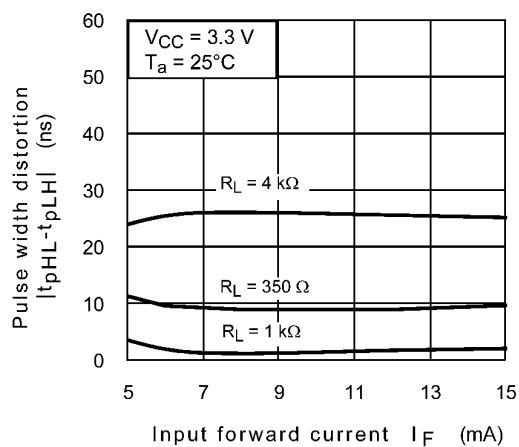


Fig. 12.2.18 $|t_{pHL} - t_{pLH}|$ - I_F

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.

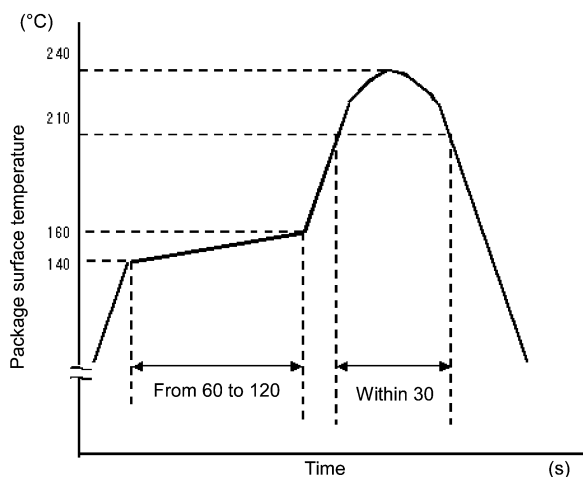


Fig. 13.1.1 An example of a temperature profile when Sn-Pb eutectic solder is used

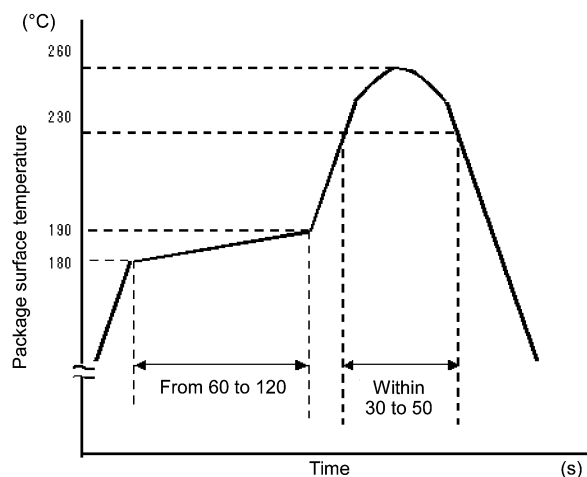
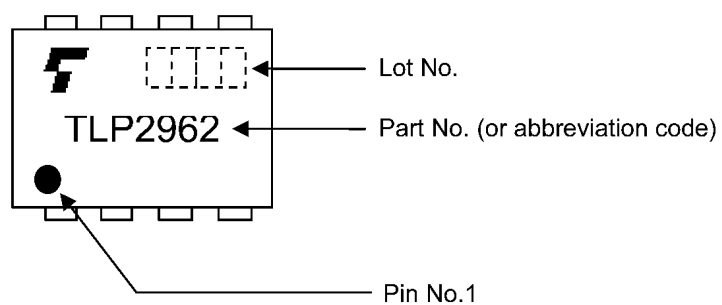


Fig. 13.1.2 An example of a temperature profile when lead(Pb)-free solder is used

- When using soldering flow (Applicable to both eutectic solder and Lead(Pb)-Free solder)
Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
Mounting condition of 260 °C within 10 seconds is recommended.
Flow soldering must be performed once.
- When using soldering Iron
Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

14. Marking

15. EN60747-5-5 Option (D4) Specification

- Part number: TLP2962 (**Note 1**)
- The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN60747.

Example: TLP2962(D4,F)

D4: EN60747 option

F: [[G]]/RoHS COMPATIBLE (**Note 2**)

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP2962(D4,F) → TLP2962

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

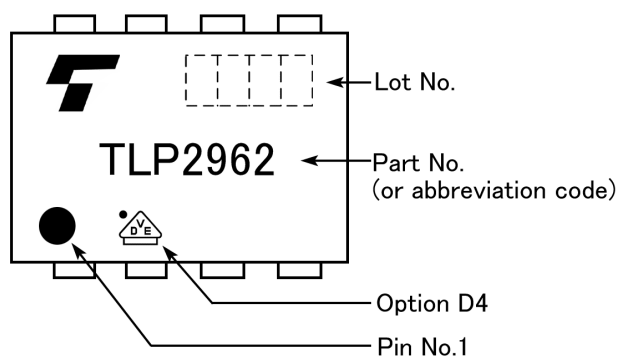
Description	Symbol	Rating	Unit
Application classification			
for rated mains voltage ≤ 600 Vrms		I-IV	—
for rated mains voltage ≤ 1000 Vrms		I-III	
Climatic classification		55 / 125 / 21	—
Pollution degree		2	—
Maximum operating insulation voltage	VIORM	890	Vpeak
Input to output test voltage, Method A $V_{pr} = 1.6 \times VIORM$, type and sample test $t_p = 10$ s, partial discharge < 5 pC	Vpr	1424	Vpeak
Input to output test voltage, Method B $V_{pr} = 1.875 \times VIORM$, 100 % production test $t_p = 1$ s, partial discharge < 5 pC	Vpr	1670	Vpeak
Highest permissible overvoltage (transient overvoltage, $t_{pr} = 60$ s)	VTR	8000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve)			
current (input current I_F , $P_{SO} = 0$)	Isi	300	mA
power (output or total power dissipation)	Pso	500	mW
temperature	Ts	150	°C
Insulation resistance			
$V_{IO} = 500$ V, $T_a = 25$ °C	Rsi	$\geq 10^{12}$	Ω
$V_{IO} = 500$ V, $T_a = 100$ °C		$\geq 10^{11}$	
$V_{IO} = 500$ V, $T_a = T_s$		$\geq 10^9$	

Fig. 15.1 EN60747 Isolation Characteristics

Minimum creepage distance	Cr	7.0 mm
Minimum clearance	Cl	7.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	175

Fig. 15.2 Insulation Related Specifications (Note)

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.


Fig. 15.3 Marking on Packing

Fig. 15.4 Marking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN60747.

Figure 1 Partial discharge measurement procedure according to EN60747
Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests,
destructive tests)

t_1, t_2 = 1 to 10 s
 t_3, t_4 = 1 s
 t_p (Measuring time for
 partial discharge) = 10 s
 t_b = 12 s
 t_{ini} = 60 s

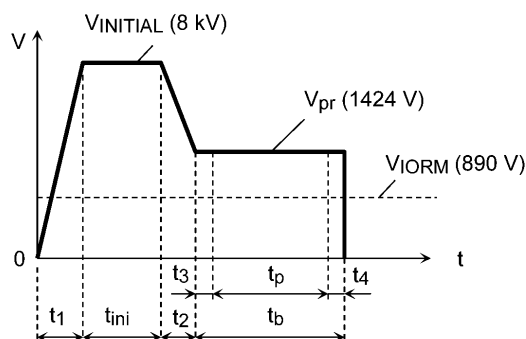


Figure 2 Partial discharge measurement procedure according to EN60747
Non-destructive test for 100 % inspection.

Method B

(for sample test, non-
destructive test)

t_3, t_4 = 0.1 s
 t_p (Measuring time for
 partial discharge) = 1 s
 t_b = 1.2 s

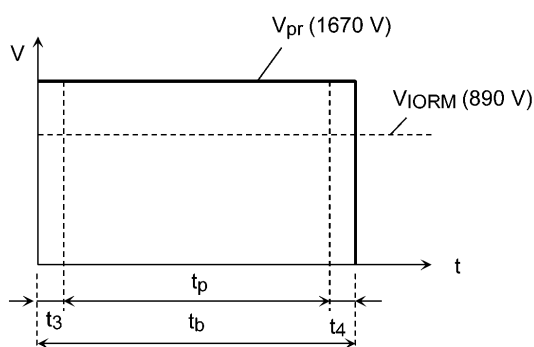


Figure 3 Dependency of maximum safety ratings on ambient temperature

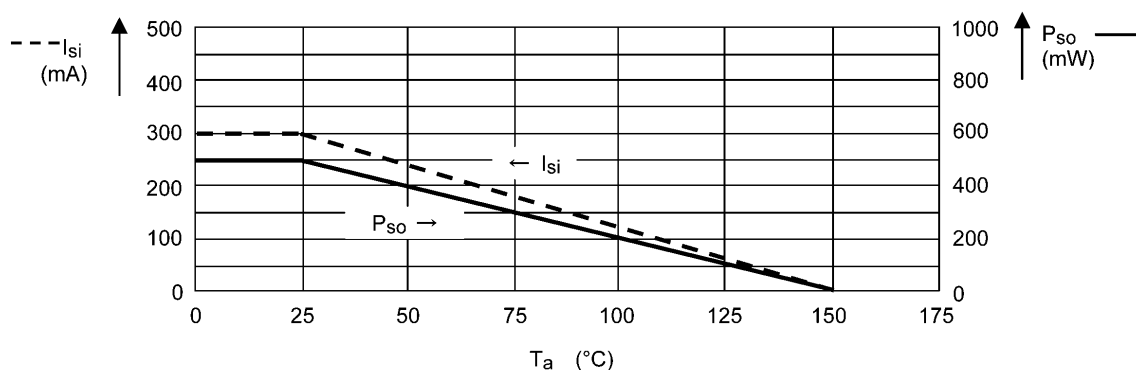
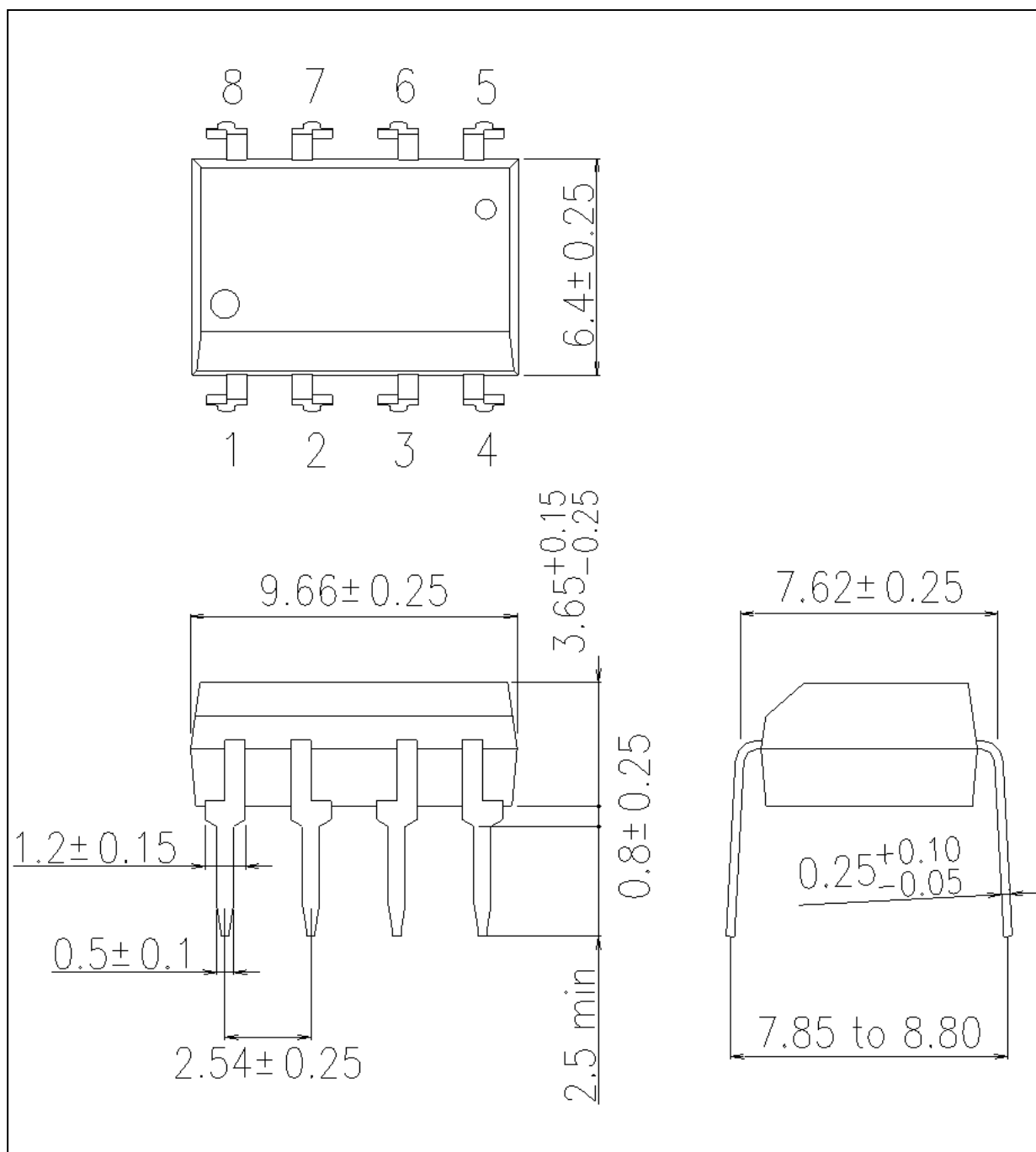


Fig. 15.5 Measurement Procedure

Package Dimensions

Unit: mm



Weight: 0.54 g (typ.)

Package Name(s)
TOSHIBA: 11-10C4S

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